NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **BLX96** is Designed for Class A Television Band IV- V Amplifier Applications Requiring High Linearity.

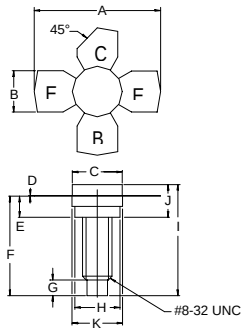
FEATURES:

- $\mathbf{P_G}$ = 7.0 dB Typical at 860 MHz
- $\mathbf{IMD_3}$ = -63 dBc Typ. at P_{REF} = 0.5 W
- ***Omnigold***™ Metallization System

MAXIMUM RATINGS

$\mathbf{I_C}$	1.0 A
$\mathbf{V_{CB}}$	45 V
$\mathbf{P_{DISS}}$	16 W @ T_C = 25 ^{O}C
$\mathbf{T_J}$	-65 ^{O}C to +200 ^{O}C
$\mathbf{T_{STG}}$	-65 ^{O}C to +150 ^{O}C
$\mathbf{\theta_{JC}}$	11 ^{O}C/W

PACKAGE STYLE .280 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 /5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

ORDER CODE: ASI10784

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$\mathbf{BV_{CEO}}$	I_C = 40 mA	24			**V**
$\mathbf{BV_{CER}}$	I_C = 40 mA R_{BE} = 10 Ω	50			**V**
$\mathbf{BV_{CBO}}$	I_C = 2 mA	45			**V**
$\mathbf{BV_{EBO}}$	I_E = 0.5 mA	3.5			**V**
$\mathbf{h_{FE}}$	V_{CE} = 20 V I_C = 250 mA	20		150	**---**
$\mathbf{C_{OB}}$	V_{CB} = 20 V f = 1.0 MHz			10	**pF**
$\mathbf{P_G}$	V_{CE} = 25 V I_C= 250 mA P_{REF} = 0.5 W	6.0	7.0		**dB**
$\mathbf{IMD_3}$	F = 860 MHz Vision = -8.0 dB Sound = -7.0 dB Chroma = -16 dB			-60	**dBc**

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